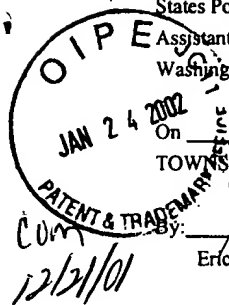


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Assistant Commissioner for Patents
Washington, D.C. 20231

PATENT
Attorney Docket No.: 018865-003600US
Client Ref. No.: 17732-9953



On December 21, 2001
TOWNSEND and TOWNSEND and CREW LLP

By: Erica L. Canonizado
Erica L. Canonizado

7a
D. Scott
2-17-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Sharp et al.

Application No.: 09/448,884

Filed: November 24, 1999

For: HYDROGEN ANNEAL FOR
CREATING AN ENHANCED TRENCH
FOR TRENCH MOSFETS

Examiner: D. Vu

Art Unit: 2818

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed September 21, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows and cancel claims 15-18. Please replace the claims currently of record with the following scannable version of pending claims 1-14 and 19-23.

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- a¹
- 1 1. (Amended) A method of forming a trench in a semiconductor substrate, the
 - 2 trench defined by an open end at a major surface of the substrate and a closed end within the body of
 - 3 the substrate, the method comprising the steps of:
 - 4 (a) forming a trench that extends a predetermined distance into the
 - 5 substrate; and
 - 6 (b) annealing the trench to: